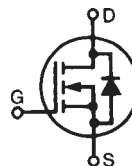


PolarHT™ HiPerFET IXFN 180N15P

Power MOSFET

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

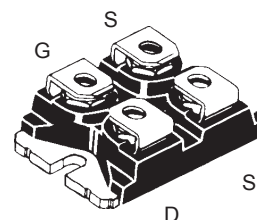


$$\begin{aligned} V_{DSS} &= 150 \text{ V} \\ I_{D25} &= 150 \text{ A} \\ R_{DS(on)} &\leq 11 \text{ m}\Omega \\ t_{rr} &\leq 200 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	150	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	150	V
V_{DSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	150	A
$I_{D(RMS)}$	External lead current limit	100	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	380	A
I_{AR}	$T_C = 25^\circ\text{C}$	60	A
E_{AR}	$T_C = 25^\circ\text{C}$	100	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	4	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	680	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
V_{ISOL}	50/60 Hz $t = 1 \text{ min}$	2500	V~
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000	V~
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
Weight		30	g

miniBLOC, SOT-227 B (IXFN)

 E153432



G = Gate D = Drain
S = Source

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- † Fast recovery diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
 - easy to drive and to protect

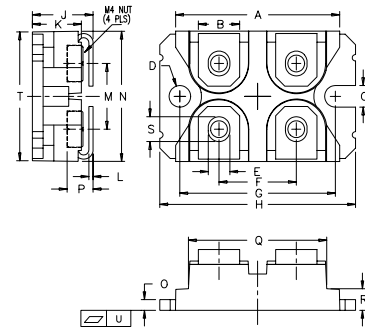
Advantages

- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			25 μA 500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 90 \text{ A}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			11 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 90\text{ A}$, pulse test	55	86	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7000	pF
C_{oss}			2250	pF
C_{rss}			515	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 90\text{ A}$ $R_G = 3.3\ \Omega$ (External)		30	ns
t_r			32	ns
$t_{d(off)}$			150	ns
t_f			36	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 90\text{ A}$		240	nC
Q_{gs}			55	nC
Q_{gd}			140	nC
R_{thJC}		0.05	0.22°C/W	
R_{thCS}			$^\circ\text{C/W}$	

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	Min.	typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			180 A
I_{SM}	Repetitive			380 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}, V_{GS} = 0\text{ V}$	0.6	6	200 ns
Q_{RM}				μC
I_{RM}				A

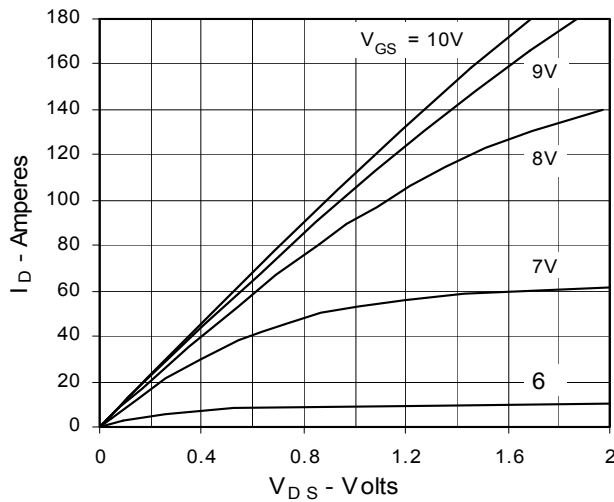
SOT-227B Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

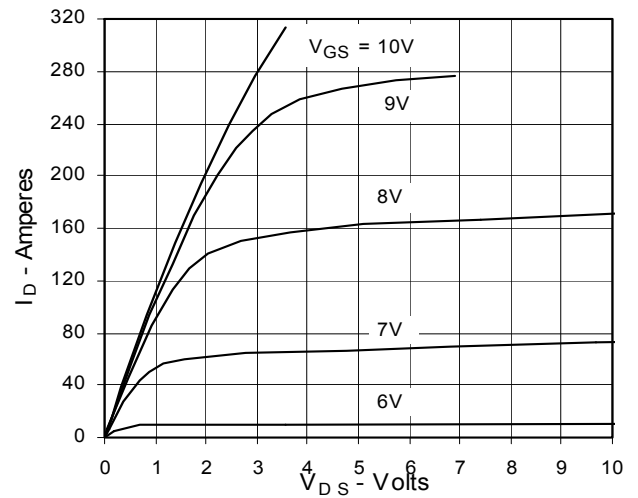
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

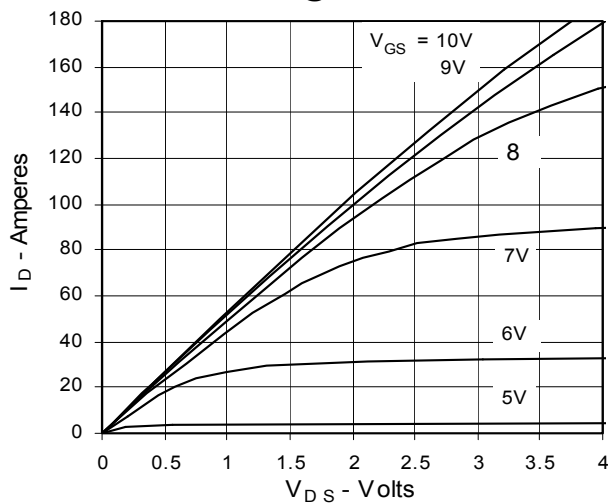
**Fig. 1. Output Characteristics
@ 25°C**



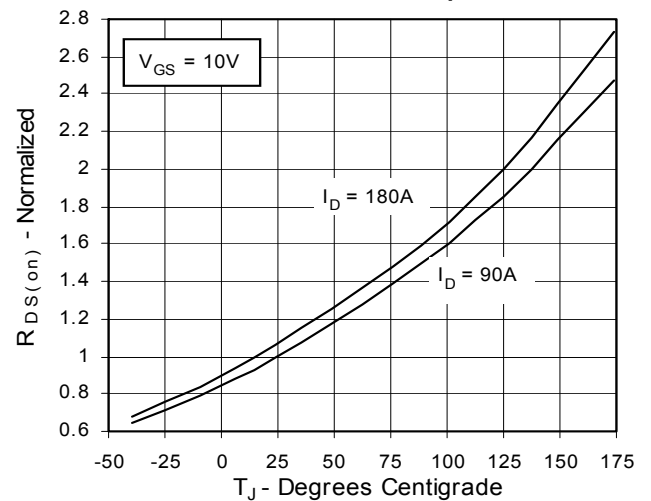
**Fig. 2. Extended Output Characteristics
@ 25°C**



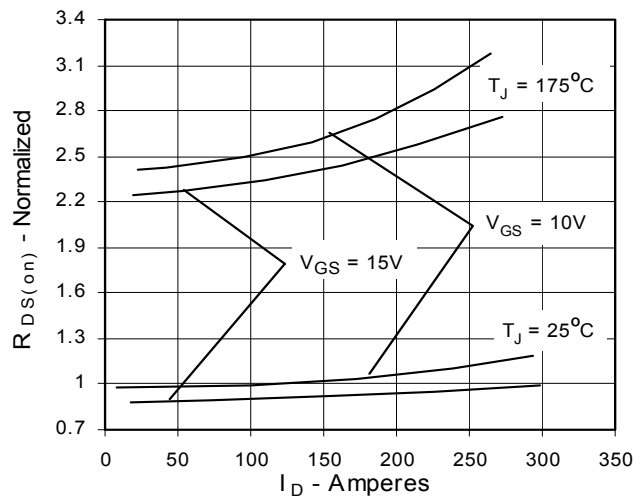
**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 90\text{A}$
Value vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 90\text{A}$
Value vs. Drain Current**



**Fig. 6. Drain Current vs. Case
Temperature**

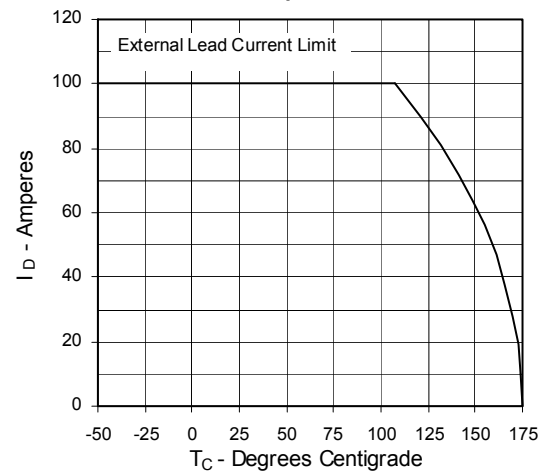


Fig. 7. Input Admittance

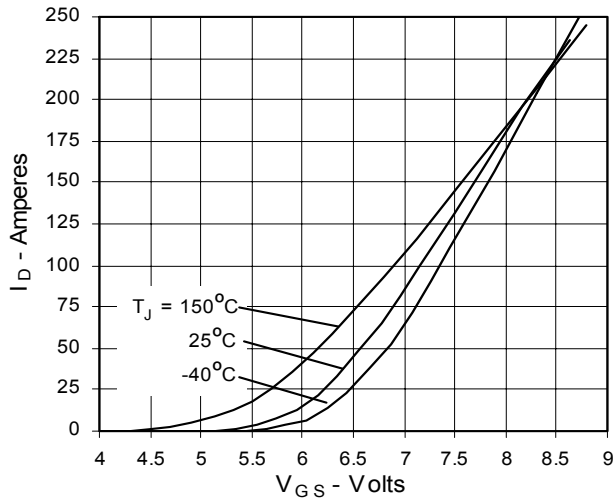


Fig. 8. Transconductance

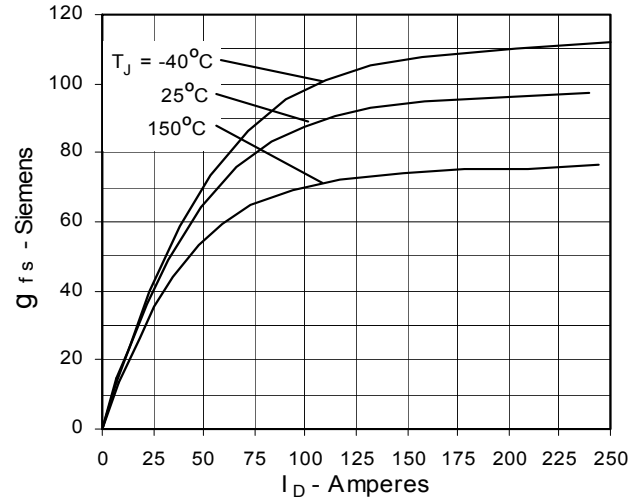


Fig. 9. Source Current vs. Source-To-Drain Voltage

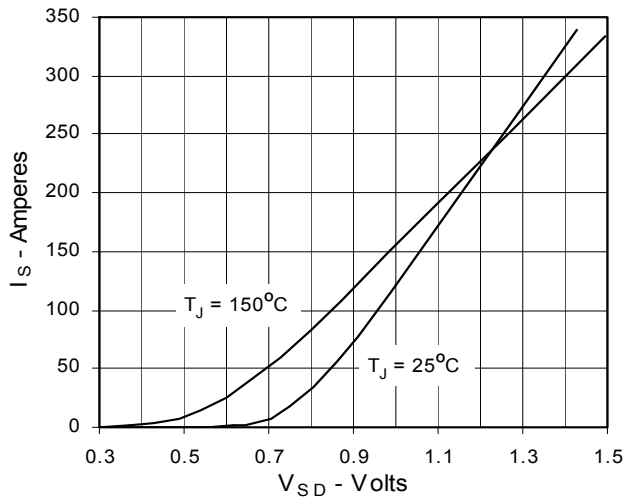


Fig. 10. Gate Charge

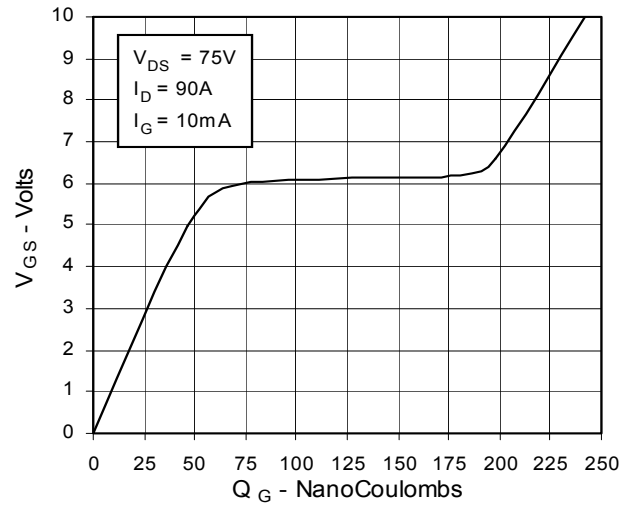


Fig. 11. Capacitance

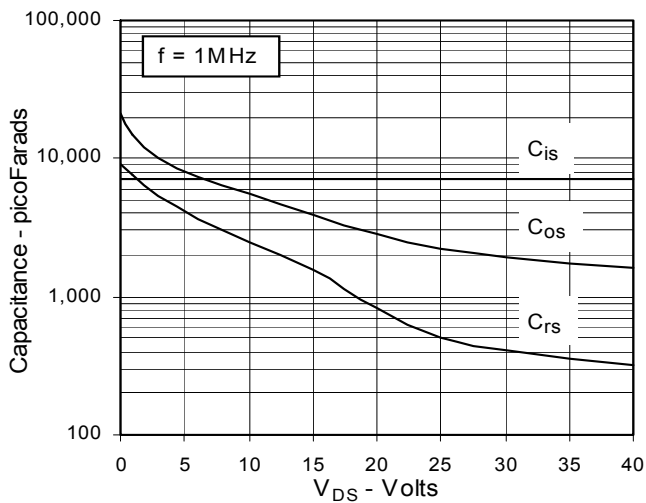


Fig. 12. Forward-Bias Safe Operating Area

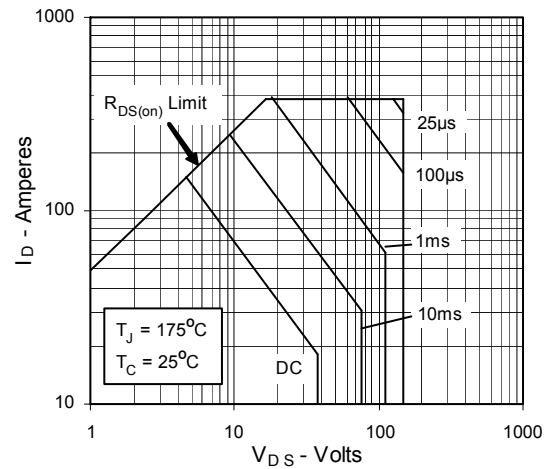


Fig. 13. Maximum Transient Thermal Resistance

